

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S78	2	"20010003019"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:15
S79	104	(elo or lateral near2 overgrow\$6) same pattern\$5 same etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:39
S80	31	etch\$5 near10 (photoresist or resist) near15 pattern\$5 near15 end\$1point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:45
S81	312	etch\$5 near10 (photoresist or resist) near15 pattern\$5 near15 over\$1etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:58
S84	68	selectiv\$6 near5 etch\$6 same (lateral near2 overgrow\$6 or elo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:59
S83	0	selectiv\$6 near5 etch\$6 near10 smooth\$6 same (lateral near2 overgrow\$6 or elo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:59
S82	238	selectiv\$6 near5 etch\$6 near10 smooth\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:59
S85	0	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) same (lateral near2 overgrow\$6 or elo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:00
S87	0	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) near15 substrte	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:01
S91	0	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) near15 substrate near2 etch\$4 near5 into	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:02

S90	2297	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) near15 substrate near2 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:02
S89	2305	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) near15 substrate near4 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:02
S88	2405	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) near15 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:02
S92	311	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) near15 substrate near2 etch\$4 near5 portion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:03
S94	45	(elo or lateral near2 overgrow\$5) near15 trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:04
S93	125	(elo or lateral near2 overgrow\$5) same trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:04
S86	90	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) and (lateral near2 overgrow\$6 or elo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48
S72	7	(etsuo near2 morita).in. and pitch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48
S47	253	offset and etch\$3 and III-V and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48
S13	36	III-V and pattern\$3 same (width or diameter or length) same second and overla\$3 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48

L4	8	(etsuo near2 morita).in. and pitch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48
L3	613	offset and etch\$3 and III-V and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48
L2	90	selectiv\$6 near5 etch\$6 near15 (photoresist or resist) and (lateral near2 overgrow\$6 or elo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48
L1	36	III-V and pattern\$3 same (width or diameter or length) same second and overla\$3 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 15:48